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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I²C, LINbus, SIO, SSU, UART/USART
Peripherals	POR, PWM, Voltage Detect, WDT
Number of I/O	75
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	2.5K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 20x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-LQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21386cnfp-30

1.1.2 Specifications

Tables 1.1 and 1.2 outline the Specifications for R8C/38C Group.

Table 1.1 Specifications for R8C/38C Group (1)

Item	Function	Specification
CPU	Central processing unit	R8C CPU core • Number of fundamental instructions: 89 • Minimum instruction execution time: 50 ns (f(XIN) = 20 MHz, VCC = 2.7 to 5.5 V) 200 ns (f(XIN) = 5 MHz, VCC = 1.8 to 5.5 V) • Multiplier: 16 bits × 16 bits → 32 bits • Multiply-accumulate instruction: 16 bits × 16 bits + 32 bits → 32 bits • Operation mode: Single-chip mode (address space: 1 Mbyte)
Memory	ROM, RAM, Data flash	Refer to **Table 1.3 Product List for R8C/38C Group**
Power Supply Voltage Detection	Voltage detection circuit	• Power-on reset • Voltage detection 3 (detection level of voltage detection 0 and voltage detection 1 selectable)
I/O Ports	Programmable I/O ports	• Input-only: 1 pin • CMOS I/O ports: 75, selectable pull-up resistor • High current drive ports: 75
Clock	Clock generation circuits	• 4 circuits: XIN clock oscillation circuit, XCIN clock oscillation circuit (32 kHz), High-speed on-chip oscillator (with frequency adjustment function), Low-speed on-chip oscillator • Oscillation stop detection: XIN clock oscillation stop detection function • Frequency divider circuit: Dividing selectable 1, 2, 4, 8, and 16 • Low power consumption modes: Standard operating mode (high-speed clock, low-speed clock, high-speed on-chip oscillator, low-speed on-chip oscillator), wait mode, stop mode
		Real-time clock (timer RE)
Interrupts		• Interrupt Vectors: 69 • External: 9 sources ($\overline{\text{INT}}$ × 5, key input × 4) • Priority levels: 7 levels
Watchdog Timer		• 14 bits × 1 (with prescaler) • Reset start selectable • Low-speed on-chip oscillator for watchdog timer selectable
DTC (Data Transfer Controller)		• 1 channel • Activation sources: 39 • Transfer modes: 2 (normal mode, repeat mode)
Timer	Timer RA	8 bits × 1 (with 8-bit prescaler) Timer mode (period timer), pulse output mode (output level inverted every period), event counter mode, pulse width measurement mode, pulse period measurement mode
	Timer RB	8 bits × 1 (with 8-bit prescaler) Timer mode (period timer), programmable waveform generation mode (PWM output), programmable one-shot generation mode, programmable wait one-shot generation mode
	Timer RC	16 bits × 1 (with 4 capture/compare registers) Timer mode (input capture function, output compare function), PWM mode (output 3 pins), PWM2 mode (PWM output pin)
	Timer RD	16 bits × 2 (with 4 capture/compare registers) Timer mode (input capture function, output compare function), PWM mode (output 6 pins), reset synchronous PWM mode (output three-phase waveforms (6 pins), sawtooth wave modulation), complementary PWM mode (output three-phase waveforms (6 pins), triangular wave modulation), PWM3 mode (PWM output 2 pins with fixed period)

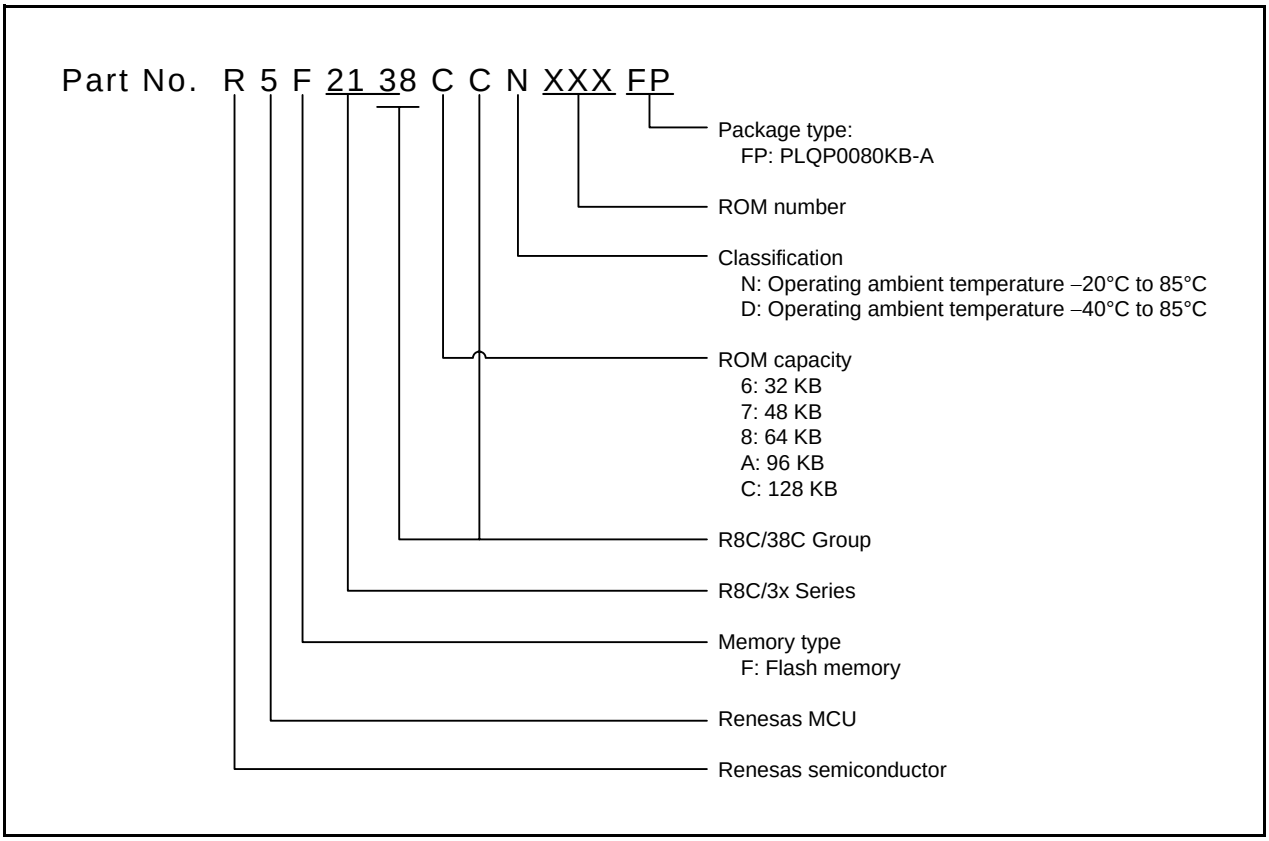


Figure 1.1 Part Number, Memory Size, and Package of R8C/38C Group

Table 1.4 Pin Name Information by Pin Number (1)

Pin Number	Control Pin	Port	I/O Pin Functions for Peripheral Modules					
			Interrupt	Timer	Serial Interface	SSU	I^2C bus	A/D Converter, D/A Converter, Comparator B
1		P5_6		(TRAO/TRGIOA)				
2		P5_5		(TRAIO)				
3		P3_2	($\overline{INT1}$/ $\overline{INT2}$)	(TRAIO/TRGCLKB)				
4		P3_0		(TRAO/TRGCLKA)				
5		P4_2						VREF
6	MODE							
7	(XCIN)	P4_3						
8	(XCOUT)	P4_4						
9	$\overline{RESET}$							
10	XOUT	P4_7						
11	VSS/AVSS							
12	XIN	P4_6						
13	VCC/AVCC							
14		P5_4		(TRCIOD)				
15		P5_3		(TRCIOC)				
16		P5_2		(TRCIOB)				
17		P5_1		(TRCIOA/TRCTRG)				
18		P5_0		(TRCCLK)				
19		P3_7		TRAO	(TXD2/SDA2/ RXD2/SCL2)	SSO	SDA	
20		P3_5		(TRCIOD)	(CLK2)	SSCK	SCL	
21		P3_4		(TRCIOC)	(TXD2/SDA2/ RXD2/SCL2)	SSI		IVREF3
22		P3_3	$\overline{INT3}$	(TRCCLK)	($\overline{CTS2}$/$\overline{RTS2}$)	$\overline{SCS}$		IVCMP3
23		P2_7		(TRDIOD1)				
24		P2_6		(TRDIOC1)				
25		P2_5		(TRDIOB1)				
26		P2_4		(TRDIOA1)				
27		P2_3		(TRDIOD0)				
28		P2_2		(TRCIOD/TRDIOB0)				
29		P2_1		(TRCIOC/TRDIOC0)				
30		P2_0	($\overline{INT1}$)	(TRCIOB/TRDIOA0/ TRDCLK)				
31		P9_3						
32		P9_2						
33		P9_1						
34		P9_0						
35		P3_6	($\overline{INT1}$)					
36		P3_1		(TRBO)				
37		P8_7						
38		P8_6						
39		P8_5		(TRFO12)				
40		P8_4		(TRFO11)				

Note:
1. Can be assigned to the pin in parentheses by a program.

1.5 Pin Functions

Tables 1.6 and 1.7 list Pin Functions.

Table 1.6 Pin Functions (1)

Item	Pin Name	I/O Type	Description
Power supply input	VCC, VSS	—	Apply 1.8 to 5.5 V to the VCC pin. Apply 0 V to the VSS pin.
Analog power supply input	AVCC, AVSS	—	Power supply for the A/D converter. Connect a capacitor between AVCC and AVSS.
Reset input	$\overline{\text{RESET}}$	I	Input “L” on this pin resets the MCU.
MODE	MODE	I	Connect this pin to VCC via a resistor.
XIN clock input	XIN	I	These pins are provided for XIN clock generation circuit I/O. Connect a ceramic resonator or a crystal oscillator between the XIN and XOUT pins. (1) To use an external clock, input it to the XOUT pin and leave the XIN pin open.
XIN clock output	XOUT	I/O	
XCIN clock input	XCIN	I	These pins are provided for XCIN clock generation circuit I/O. Connect a crystal oscillator between the XCIN and XCOUT pins. (1) To use an external clock, input it to the XCIN pin and leave the XCOUT pin open.
XCIN clock output	XCOUT	O	
$\overline{\text{INT}}$ interrupt input	$\overline{\text{INT0}}$ to $\overline{\text{INT4}}$	I	$\overline{\text{INT}}$ interrupt input pins.
Key input interrupt	$\overline{\text{KI0}}$ to $\overline{\text{KI3}}$	I	Key input interrupt input pins.
Timer RA	TRAIO	I/O	Timer RA I/O pin.
	TRAO	O	Timer RA output pin.
Timer RB	TRBO	O	Timer RB output pin.
Timer RC	TRCCLK	I	External clock input pin.
	TRCTRG	I	External trigger input pin.
	TRCIOA, TRCIOB, TRCIOC, TRCIOD	I/O	Timer RC I/O pins.
Timer RD	TRDIOA0, TRDIOA1, TRDIOB0, TRDIOB1, TRDIOC0, TRDIOC1, TRDIOD0, TRDIOD1	I/O	Timer RD I/O pins.
	TRDCLK	I	External clock input pin.
Timer RE	TREO	O	Divided clock output pin.
Timer RF	TRFO00, TRFO10, TRFO01,TRFO11, TRFO02,TRFO12	O	Timer RF output pins.
	TRFI	I	Timer RF input pin.
Timer RG	TRGIOA, TRGIOB	I/O	Timer RG I/O ports.
	TRGCLKA, TRGCLKB	I	External clock input pins.
Serial interface	CLK0, CLK1, CLK2	I/O	Transfer clock I/O pins.
	RXD0, RXD1, RXD2	I	Serial data input pins.
	TXD0, TXD1, TXD2	O	Serial data output pins.
	$\overline{\text{CTS2}}$	I	Transmission control input pin.
	$\overline{\text{RTS2}}$	O	Reception control output pin.
	SCL2	I/O	I^2C mode clock I/O pin.
	SDA2	I/O	I^2C mode data I/O pin.

I: Input O: Output I/O: Input and output

Note:

1. Refer to the oscillator manufacturer for oscillation characteristics.

2.8.7 Interrupt Enable Flag (I)

The I flag enables maskable interrupts.
Interrupts are disabled when the I flag is set to 0, and are enabled when the I flag is set to 1. The I flag is set to 0 when an interrupt request is acknowledged.

2.8.8 Stack Pointer Select Flag (U)

ISP is selected when the U flag is set to 0; USP is selected when the U flag is set to 1.
The U flag is set to 0 when a hardware interrupt request is acknowledged or the INT instruction of software interrupt numbers 0 to 31 is executed.

2.8.9 Processor Interrupt Priority Level (IPL)

IPL is 3 bits wide and assigns processor interrupt priority levels from level 0 to level 7.
If a requested interrupt has higher priority than IPL, the interrupt is enabled.

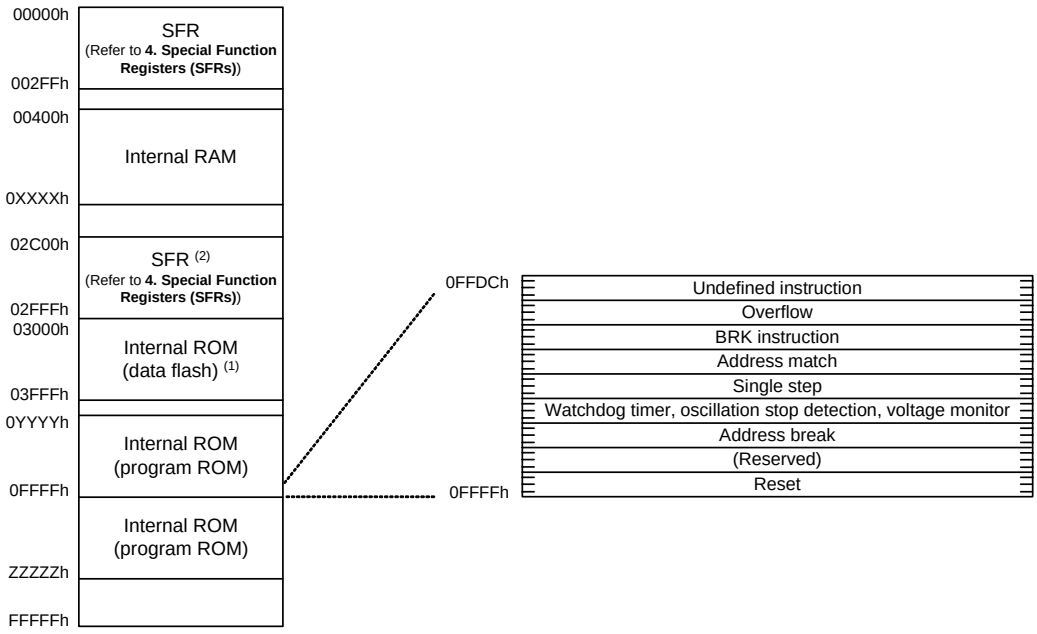
2.8.10 Reserved Bit

If necessary, set to 0. When read, the content is undefined.

3. Memory

3.1 R8C/38C Group

Figure 3.1 is a Memory Map of R8C/38C Group. The R8C/38C Group has a 1-Mbyte address space from addresses 00000h to FFFFFh. The internal ROM (program ROM) is allocated lower addresses, beginning with address 0FFFFh. For example, a 64-Kbyte internal ROM area is allocated addresses 04000h to 13FFFh.
The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. The starting address of each interrupt routine is stored here.
The internal ROM (data flash) is allocated addresses 03000h to 03FFFh.
The internal RAM is allocated higher addresses, beginning with address 00400h. For example, a 6-Kbyte internal RAM area is allocated addresses 00400h to 01BFFh. The internal RAM is used not only for data storage but also as a stack area when a subroutine is called or when an interrupt request is acknowledged.
Special function registers (SFRs) are allocated addresses 00000h to 002FFh and 02C00h to 02FFFh (the SFR areas for the DTC and other modules). Peripheral function control registers are allocated here. All unallocated spaces within the SFRs are reserved and cannot be accessed by users.



Notes:
1. The data flash indicates block A (1 Kbyte), block B (1 Kbyte), block C (1 Kbyte), and block D (1 Kbyte).
2. The SFR areas for the DTC and other modules are allocated to addresses 02C00h to 02FFFh.
3. The blank areas are reserved and cannot be accessed by users.

Part Number	Internal ROM			Internal RAM	
	Size	Address 0YYYYh	Address ZZZZZh	Size	Address 0XXXXh
R5F21386CNFP, R5F21386CDFP, R5F21386CNXXXFP, R5F21386CDXXXFP	32 Kbytes	08000h	–	2.5 Kbytes	00DFFh
R5F21387CNFP, R5F21387CDFP, R5F21387CNXXXFP, R5F21387CDXXXFP	48 Kbytes	04000h	–	4 Kbytes	013FFh
R5F21388CNFP, R5F21388CDFP, R5F21388CNXXXFP, R5F21388CDXXXFP	64 Kbytes	04000h	13FFFh	6 Kbytes	01BFFh
R5F2138ACNFP, R5F2138ACDFP, R5F2138ACNXXXFP, R5F2138ACDXXXFP	96 Kbytes	04000h	1BFFFh	8 Kbytes	023FFh
R5F2138CCNFP, R5F2138CCDFP, R5F2138CCNXXXFP, R5F2138CCDXXXFP	128 Kbytes	04000h	23FFFh	10 Kbytes	02BFFh

Figure 3.1 Memory Map of R8C/38C Group

Table 4.2 SFR Information (2) (1)

Address	Register	Symbol	After Reset
003Ah	Voltage Monitor 2 Circuit Control Register	VW2C	10000010b
003Bh			
003Ch			
003Dh			
003Eh			
003Fh			
0040h			
0041h	Flash Memory Ready Interrupt Control Register	FMRDYIC	XXXXX000b
0042h			
0043h			
0044h			
0045h			
0046h	INT4 Interrupt Control Register	INT4IC	XX00X000b
0047h	Timer RC Interrupt Control Register	TRCIC	XXXXX000b
0048h	Timer RD0 Interrupt Control Register	TRD0IC	XXXXX000b
0049h	Timer RD1 Interrupt Control Register	TRD1IC	XXXXX000b
004Ah	Timer RE Interrupt Control Register	TREIC	XXXXX000b
004Bh	UART2 Transmit Interrupt Control Register	S2TIC	XXXXX000b
004Ch	UART2 Receive Interrupt Control Register	S2RIC	XXXXX000b
004Dh	Key Input Interrupt Control Register	KUPIC	XXXXX000b
004Eh	A/D Conversion Interrupt Control Register	ADIC	XXXXX000b
004Fh	SSU Interrupt Control Register/IIC bus Interrupt Control Register (2)	SSUIC/IICIC	XXXXX000b
0050h	Timer RF Compare 1 Interrupt Control Register	CMP1IC	XXXXX000b
0051h	UART0 Transmit Interrupt Control Register	S0TIC	XXXXX000b
0052h	UART0 Receive Interrupt Control Register	S0RIC	XXXXX000b
0053h	UART1 Transmit Interrupt Control Register	S1TIC	XXXXX000b
0054h	UART1 Receive Interrupt Control Register	S1RIC	XXXXX000b
0055h	INT2 Interrupt Control Register	INT2IC	XX00X000b
0056h	Timer RA Interrupt Control Register	TRAIC	XXXXX000b
0057h			
0058h	Timer RB Interrupt Control Register	TRBIC	XXXXX000b
0059h	INT1 Interrupt Control Register	INT1IC	XX00X000b
005Ah	INT3 Interrupt Control Register	INT3IC	XX00X000b
005Bh	Timer RF Interrupt Control Register	TRFIC	XXXXX000b
005Ch	Timer RF Compare 0 Interrupt Control Register	CMP0IC	XXXXX000b
005Dh	INT0 Interrupt Control Register	INT0IC	XX00X000b
005Eh	UART2 Bus Collision Detection Interrupt Control Register	U2BCNIC	XXXXX000b
005Fh	Timer RF Capture Interrupt Control Register	CAPIC	XXXXX000b
0060h			
0061h			
0062h			
0063h			
0064h			
0065h			
0066h			
0067h			
0068h			
0069h			
006Ah			
006Bh	Timer RG Interrupt Control Register	TRGIC	XXXXX000b
006Ch			
006Dh			
006Eh			
006Fh			
0070h			
0071h			
0072h	Voltage Monitor 1 Interrupt Control Register	VCMP1IC	XXXXX000b
0073h	Voltage Monitor 2 Interrupt Control Register	VCMP2IC	XXXXX000b
0074h			
0075h			
0076h			
0077h			
0078h			
0079h			
007Ah			
007Bh			
007Ch			
007Dh			
007Eh			
007Fh			

X: Undefined

Notes:

1. The blank areas are reserved and cannot be accessed by users.
2. Selectable by the IICSEL bit in the SSUIICSR register.

Table 4.4 SFR Information (4) (1)

Address	Register	Symbol	After Reset
00C0h	A/D Register 0	AD0	XXh
00C1h			000000XXb
00C2h	A/D Register 1	AD1	XXh
00C3h			000000XXb
00C4h	A/D Register 2	AD2	XXh
00C5h			000000XXb
00C6h	A/D Register 3	AD3	XXh
00C7h			000000XXb
00C8h	A/D Register 4	AD4	XXh
00C9h			000000XXb
00CAh	A/D Register 5	AD5	XXh
00CBh			000000XXb
00CCh	A/D Register 6	AD6	XXh
00CDh			000000XXb
00CEh	A/D Register 7	AD7	XXh
00CFh			000000XXb
00D0h			
00D1h			
00D2h			
00D3h			
00D4h	A/D Mode Register	ADMOD	00h
00D5h	A/D Input Select Register	ADINSEL	11000000b
00D6h	A/D Control Register 0	ADCON0	00h
00D7h	A/D Control Register 1	ADCON1	00h
00D8h	D/A0 Register	DA0	00h
00D9h	D/A1 Register	DA1	00h
00DAh			
00DBh			
00DCh	D/A Control Register	DACON	00h
00DDh			
00DEh			
00DFh			
00E0h	Port P0 Register	P0	XXh
00E1h	Port P1 Register	P1	XXh
00E2h	Port P0 Direction Register	PD0	00h
00E3h	Port P1 Direction Register	PD1	00h
00E4h	Port P2 Register	P2	XXh
00E5h	Port P3 Register	P3	XXh
00E6h	Port P2 Direction Register	PD2	00h
00E7h	Port P3 Direction Register	PD3	00h
00E8h	Port P4 Register	P4	XXh
00E9h	Port P5 Register	P5	XXh
00EAh	Port P4 Direction Register	PD4	00h
00EBh	Port P5 Direction Register	PD5	00h
00ECh	Port P6 Register	P6	XXh
00EDh	Port P7 Register	P7	XXh
00EEh	Port P6 Direction Register	PD6	00h
00EFh	Port P7 Direction Register	PD7	00h
00F0h	Port P8 Register	P8	XXh
00F1h	Port P9 Register	P9	XXh
00F2h	Port P8 Direction Register	PD8	00h
00F3h	Port P9 Direction Register	PD9	00h
00F4h			
00F5h			
00F6h			
00F7h			
00F8h			
00F9h			
00FAh			
00FBh			
00FCh			
00FDh			
00FEh			
00FFh			

X: Undefined

Note:

1. The blank areas are reserved and cannot be accessed by users.

Table 5.2 Recommended Operating Conditions (1)

Symbol	Parameter				Conditions	Standard			Unit
						Min.	Typ.	Max.	
V_{CC}/AV_{CC}	Supply voltage					1.8	—	5.5	V
V_{SS}/AV_{SS}	Supply voltage					—	0	—	V
V_{IH}	Input “H” voltage	Other than CMOS input				0.8 V_{CC}	—	V_{CC}	V
		CMOS input	Input level switching function (I/O port)	Input level selection: 0.35 V_{CC}	4.0 V ≤ V_{CC} ≤ 5.5 V	0.5 V_{CC}	—	V_{CC}	V
					2.7 V ≤ V_{CC} < 4.0 V	0.55 V_{CC}	—	V_{CC}	V
					1.8 V ≤ V_{CC} < 2.7 V	0.65 V_{CC}	—	V_{CC}	V
				Input level selection: 0.5 V_{CC}	4.0 V ≤ V_{CC} ≤ 5.5 V	0.65 V_{CC}	—	V_{CC}	V
					2.7 V ≤ V_{CC} < 4.0 V	0.7 V_{CC}	—	V_{CC}	V
					1.8 V ≤ V_{CC} < 2.7 V	0.8 V_{CC}	—	V_{CC}	V
				Input level selection: 0.7 V_{CC}	4.0 V ≤ V_{CC} ≤ 5.5 V	0.85 V_{CC}	—	V_{CC}	V
					2.7 V ≤ V_{CC} < 4.0 V	0.85 V_{CC}	—	V_{CC}	V
					1.8 V ≤ V_{CC} < 2.7 V	0.85 V_{CC}	—	V_{CC}	V
		External clock input (XOUT)				1.2	—	V_{CC}	V
V_{IL}	Input “L” voltage	Other than CMOS input				0	—	0.2 V_{CC}	V
		CMOS input	Input level switching function (I/O port)	Input level selection: 0.35 V_{CC}	4.0 V ≤ V_{CC} ≤ 5.5 V	0	—	0.2 V_{CC}	V
					2.7 V ≤ V_{CC} < 4.0 V	0	—	0.2 V_{CC}	V
					1.8 V ≤ V_{CC} < 2.7 V	0	—	0.2 V_{CC}	V
				Input level selection: 0.5 V_{CC}	4.0 V ≤ V_{CC} ≤ 5.5 V	0	—	0.4 V_{CC}	V
					2.7 V ≤ V_{CC} < 4.0 V	0	—	0.3 V_{CC}	V
					1.8 V ≤ V_{CC} < 2.7 V	0	—	0.2 V_{CC}	V
				Input level selection: 0.7 V_{CC}	4.0 V ≤ V_{CC} ≤ 5.5 V	0	—	0.55 V_{CC}	V
					2.7 V ≤ V_{CC} < 4.0 V	0	—	0.45 V_{CC}	V
					1.8 V ≤ V_{CC} < 2.7 V	0	—	0.35 V_{CC}	V
		External clock input (XOUT)				0	—	0.4	V
$I_{OH(sum)}$	Peak sum output “H” current	Sum of all pins $I_{OH(peak)}$				—	—	–160	mA
$I_{OH(sum)}$	Average sum output “H” current	Sum of all pins $I_{OH(avg)}$				—	—	–80	mA
$I_{OH(peak)}$	Peak output “H” current	Drive capacity Low				—	—	–10	mA
		Drive capacity High				—	—	–40	mA
$I_{OH(avg)}$	Average output “H” current	Drive capacity Low				—	—	–5	mA
		Drive capacity High				—	—	–20	mA
$I_{OL(sum)}$	Peak sum output “L” current	Sum of all pins $I_{OL(peak)}$				—	—	160	mA
$I_{OL(sum)}$	Average sum output “L” current	Sum of all pins $I_{OL(avg)}$				—	—	80	mA
$I_{OL(peak)}$	Peak output “L” current	Drive capacity Low				—	—	10	mA
		Drive capacity High				—	—	40	mA
$I_{OL(avg)}$	Average output “L” current	Drive capacity Low				—	—	5	mA
		Drive capacity High				—	—	20	mA
$f_{(XIN)}$	XIN clock input oscillation frequency				2.7 V ≤ V_{CC} ≤ 5.5 V	—	—	20	MHz
					1.8 V ≤ V_{CC} < 2.7 V	—	—	5	MHz
$f_{(XCIN)}$	XCIN clock input oscillation frequency				1.8 V ≤ V_{CC} ≤ 5.5 V	—	32.768	50	kHz
fOCO40M	When used as the count source for timer RC, timer RD or timer RG (3)				2.7 V ≤ V_{CC} ≤ 5.5 V	32	—	40	MHz
fOCO-F	fOCO-F frequency				2.7 V ≤ V_{CC} ≤ 5.5 V	—	—	20	MHz
					1.8 V ≤ V_{CC} < 2.7 V	—	—	5	MHz
—	System clock frequency				2.7 V ≤ V_{CC} ≤ 5.5 V	—	—	20	MHz
					1.8 V ≤ V_{CC} < 2.7 V	—	—	5	MHz
$f_{(BCLK)}$	CPU clock frequency				2.7 V ≤ V_{CC} ≤ 5.5 V	—	—	20	MHz
					1.8 V ≤ V_{CC} < 2.7 V	—	—	5	MHz

Notes:
1. V_{CC} = 1.8 to 5.5 V and T_{opr} = –20 to 85 °C (N version)/–40 to 85 °C (D version), unless otherwise specified.
2. The average output current indicates the average value of current measured during 100 ms.
3. fOCO40M can be used as the count source for timer RC, timer RD, or timer RG in the range of V_{CC} = 2.7 to 5.5 V.

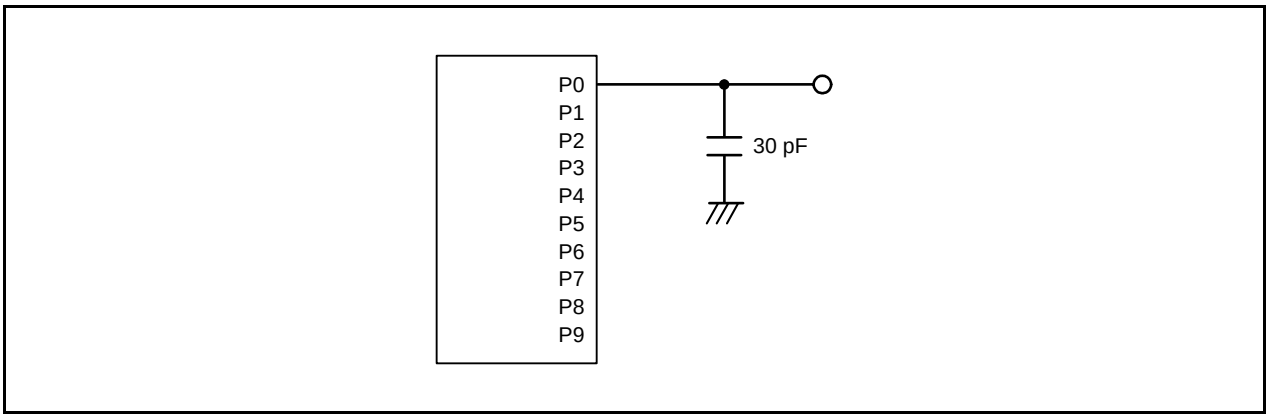


Figure 5.1 Ports P0 to P9 Timing Measurement Circuit

Table 5.3 A/D Converter Characteristics

Symbol	Parameter		Conditions		Standard			Unit
					Min.	Typ.	Max.	
—	Resolution		V_{ref} = AV_{CC}		—	—	10	Bit
—	Absolute accuracy	10-bit mode	V_{ref} = AV_{CC} = 5.0 V	AN0 to AN7 input, AN8 to AN11 input, AN12 to AN19 input	—	—	±3	LSB
			V_{ref} = AV_{CC} = 3.3 V	AN0 to AN7 input, AN8 to AN11 input, AN12 to AN19 input	—	—	±5	LSB
			V_{ref} = AV_{CC} = 3.0 V	AN0 to AN7 input, AN8 to AN11 input, AN12 to AN19 input	—	—	±5	LSB
			V_{ref} = AV_{CC} = 2.2 V	AN0 to AN7 input, AN8 to AN11 input, AN12 to AN19 input	—	—	±5	LSB
		8-bit mode	V_{ref} = AV_{CC} = 5.0 V	AN0 to AN7 input, AN8 to AN11 input, AN12 to AN19 input	—	—	±2	LSB
			V_{ref} = AV_{CC} = 3.3 V	AN0 to AN7 input, AN8 to AN11 input, AN12 to AN19 input	—	—	±2	LSB
			V_{ref} = AV_{CC} = 3.0 V	AN0 to AN7 input, AN8 to AN11 input, AN12 to AN19 input	—	—	±2	LSB
			V_{ref} = AV_{CC} = 2.2 V	AN0 to AN7 input, AN8 to AN11 input, AN12 to AN19 input	—	—	±2	LSB
ϕAD	A/D conversion clock		4.0 V ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	—	20	MHz
			3.2 V ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	—	16	MHz
			2.7 V ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	—	10	MHz
			2.2 V ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	—	5	MHz
—	Tolerance level impedance				—	3	—	kΩ
t_{CONV}	Conversion time	10-bit mode	V_{ref} = AV_{CC} = 5.0 V, ϕAD = 20 MHz		2.2	—	—	µs
		8-bit mode	V_{ref} = AV_{CC} = 5.0 V, ϕAD = 20 MHz		2.2	—	—	µs
t_{SAMP}	Sampling time		ϕAD = 20 MHz		0.8	—	—	µs
I_{Vref}	V_{ref} current		V_{CC} = 5.0 V, XIN = f1 = ϕAD = 20 MHz		—	45	—	µA
V_{ref}	Reference voltage				2.2	—	AV_{CC}	V
V_{IA}	Analog input voltage (3)				0	—	V_{ref}	V
OCVREF	On-chip reference voltage		2 MHz ≤ ϕAD ≤ 4 MHz		1.19	1.34	1.49	V

Notes:
1. V_{CC}/AV_{CC} = V_{ref} = 2.2 to 5.5 V, V_{SS} = 0 V, and T_{opr} = –20 to 85 °C (N version)/–40 to 85 °C (D version), unless otherwise specified.
2. The A/D conversion result will be undefined in wait mode, stop mode, when the flash memory stops, and in low-current-consumption mode. Do not perform A/D conversion in these states or transition to these states during A/D conversion.
3. When the analog input voltage is over the reference voltage, the A/D conversion result will be 3FFh in 10-bit mode and FFh in 8-bit mode.

Table 5.6 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
—	Program/erase endurance (2)		1,000 (3)	—	—	times
—	Byte program time		—	80	500	µs
—	Block erase time		—	0.3	—	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		—	—	5 + CPU clock × 3 cycles	ms
—	Interval from erase start/restart until following suspend request		0	—	—	µs
—	Time from suspend until erase restart		—	—	30 + CPU clock × 1 cycle	µs
$t_{d(CMDRST-READY)}$	Time from when command is forcibly stopped until reading is enabled		–	–	30 + CPU clock × 1 cycle	µs
—	Program, erase voltage		2.7	—	5.5	V
—	Read voltage		1.8	—	5.5	V
—	Program, erase temperature		0	—	60	°C
—	Data hold time (7)	Ambient temperature = 55 °C	20	—	—	year

Notes:
1. V_{CC} = 2.7 to 5.5 V and T_{opr} = 0 to 60 °C, unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 1,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one. However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed.)
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.7 Flash Memory (Data flash Block A to Block D) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
—	Program/erase endurance (2)		10,000 (3)	—	—	times
—	Byte program time (program/erase endurance ≤ 1,000 times)		—	160	1500	µs
—	Byte program time (program/erase endurance > 1,000 times)		—	300	1500	µs
—	Block erase time (program/erase endurance ≤ 1,000 times)		—	0.2	1	s
—	Block erase time (program/erase endurance > 1,000 times)		—	0.3	1	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		—	—	5 + CPU clock × 3 cycles	ms
—	Interval from erase start/restart until following suspend request		0	—	—	µs
—	Time from suspend until erase restart		—	—	30 + CPU clock × 1 cycle	µs
$t_{d(CMDRST-READY)}$	Time from when command is forcibly stopped until reading is enabled		–	–	30 + CPU clock × 1 cycle	µs
—	Program, erase voltage		2.7	—	5.5	V
—	Read voltage		1.8	—	5.5	V
—	Program, erase temperature		–20 (7)	—	85	°C
—	Data hold time (8)	Ambient temperature = 55 °C	20	—	—	year

Notes:
1. V_{CC} = 2.7 to 5.5 V and T_{opr} = –20 to 85 °C (N version)/–40 to 85 °C (D version), unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one. However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed.)
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the erasure endurance between blocks A to D can further reduce the actual erasure endurance. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. –40 °C for D version.
8. The data hold time includes time that the power supply is off or the clock is not supplied.

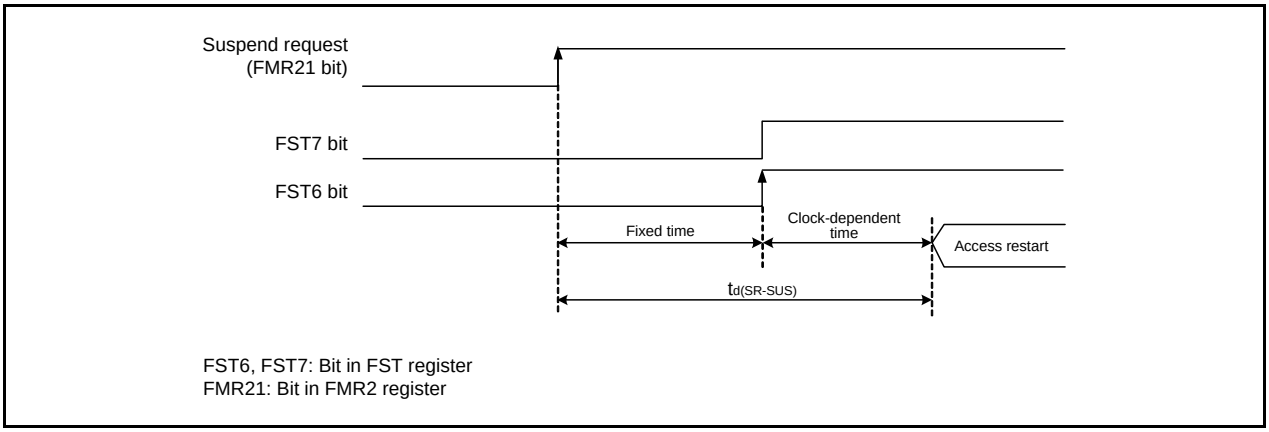


Figure 5.2 Time delay until Suspend

Table 5.12 High-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
—	High-speed on-chip oscillator frequency after reset	V_{CC} = 1.8 V to 5.5 V −20 °C ≤ Topr ≤ 85 °C	38.4	40	41.6	MHz
		V_{CC} = 1.8 V to 5.5 V −40 °C ≤ Topr ≤ 85 °C	38.0	40	42.0	MHz
	High-speed on-chip oscillator frequency when the FRA4 register correction value is written into the FRA1 register and the FRA5 register correction value into the FRA3 register (2)	V_{CC} = 1.8 V to 5.5 V −20 °C ≤ Topr ≤ 85 °C	35.389	36.864	38.338	MHz
		V_{CC} = 1.8 V to 5.5 V −40 °C ≤ Topr ≤ 85 °C	35.020	36.864	38.707	MHz
	High-speed on-chip oscillator frequency when the FRA6 register correction value is written into the FRA1 register and the FRA7 register correction value into the FRA3 register	V_{CC} = 1.8 V to 5.5 V −20 °C ≤ Topr ≤ 85 °C	30.72	32	33.28	MHz
		V_{CC} = 1.8 V to 5.5 V −40 °C ≤ Topr ≤ 85 °C	30.40	32	33.60	MHz
—	Oscillation stability time	V_{CC} = 5.0 V, T_{opr} = 25 °C	—	0.5	3	ms
—	Self power consumption at oscillation	V_{CC} = 5.0 V, T_{opr} = 25 °C	—	400	—	µA

Notes:
1. V_{CC} = 1.8 to 5.5 V and T_{opr} = −20 to 85 °C (N version)/−40 to 85 °C (D version), unless otherwise specified.
2. This enables the setting errors of bit rates such as 9600 bps and 38400 bps to be 0% when the serial interface is used in UART mode.

Table 5.13 Low-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO-S	Low-speed on-chip oscillator frequency		60	125	250	kHz
—	Oscillation stability time	V_{CC} = 5.0 V, T_{opr} = 25 °C	—	30	100	µs
—	Self power consumption at oscillation	V_{CC} = 5.0 V, T_{opr} = 25 °C	—	2	—	µA

Note:
1. V_{CC} = 1.8 to 5.5 V and T_{opr} = −20 to 85 °C (N version)/−40 to 85 °C (D version), unless otherwise specified.

Table 5.14 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
$t_{d(P-R)}$	Time for internal power supply stabilization during power-on (2)		—	—	2,000	µs

Notes:
1. The measurement condition is V_{CC} = 1.8 to 5.5 V and T_{opr} = 25 °C.
2. Waiting time until the internal power supply generation circuit stabilizes during power-on.

Table 5.17 Electrical Characteristics (1) [4.2 V ≤ Vcc ≤ 5.5 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output "H" voltage	Other than XOUT	Drive capacity High V_{CC} = 5 V	I_{OH} = –20 mA	V_{CC} – 2.0	—	V_{CC}	V
			Drive capacity Low V_{CC} = 5 V	I_{OH} = –5 mA	V_{CC} – 2.0	—	V_{CC}	V
		XOUT	V_{CC} = 5 V	I_{OH} = –200 µA	1.0	—	V_{CC}	V
V_{OL}	Output "L" voltage	Other than XOUT	Drive capacity High V_{CC} = 5 V	I_{OL} = 20 mA	—	—	2.0	V
			Drive capacity Low V_{CC} = 5 V	I_{OL} = 5 mA	—	—	2.0	V
		XOUT	V_{CC} = 5 V	I_{OL} = 200 µA	—	—	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT2}$, $\overline{INT3}$, $\overline{INT4}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, TRBO, TRCIOA, TRCIOB, TRCIOC, TRCIOD, TRDIOA0, TRDIOB0, TRDIOC0, TRDIOD0, TRDIOA1, TRDIOB1, TRDIOC1, TRDIOD1, TRCTRG, TRCCLK, TRFI, $\overline{TRGIOA}$, $\overline{TRGIOB}$, $\overline{ADTRG}$, RXD0, RXD1, RXD2, CLK0, CLK1, CLK2, SSI, SCL, SDA, SSO			0.1	1.2	—	V
		$\overline{RESET}$			0.1	1.2	—	V
I_{IH}	Input "H" current		V_I = 5 V, V_{CC} = 5.0 V		—	—	5.0	µA
I_{IL}	Input "L" current		V_I = 0 V, V_{CC} = 5.0 V		—	—	–5.0	µA
R_{PULLUP}	Pull-up resistance		V_I = 0 V, V_{CC} = 5.0 V		25	50	100	kΩ
R_{fXIN}	Feedback resistance	XIN			—	0.3	—	MΩ
R_{fXCIN}	Feedback resistance	XCIN			—	8	—	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	—	—	V

Note:
1. 4.2 V ≤ V_{CC} ≤ 5.5 V, T_{opr} = –20 to 85 °C (N version)/–40 to 85 °C (D version), and f(XIN) = 20 MHz, unless otherwise specified.

Table 5.22 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	200	—	ns
$t_{W(CKH)}$	CLKi input “H” width	100	—	ns
$t_{W(CKL)}$	CLKi input “L” width	100	—	ns
$t_{d(C-Q)}$	TXDi output delay time	—	50	ns
$t_{h(C-Q)}$	TXDi hold time	0	—	ns
$t_{su(D-C)}$	RXDi input setup time	50	—	ns
$t_{h(C-D)}$	RXDi input hold time	90	—	ns

i = 0 to 2

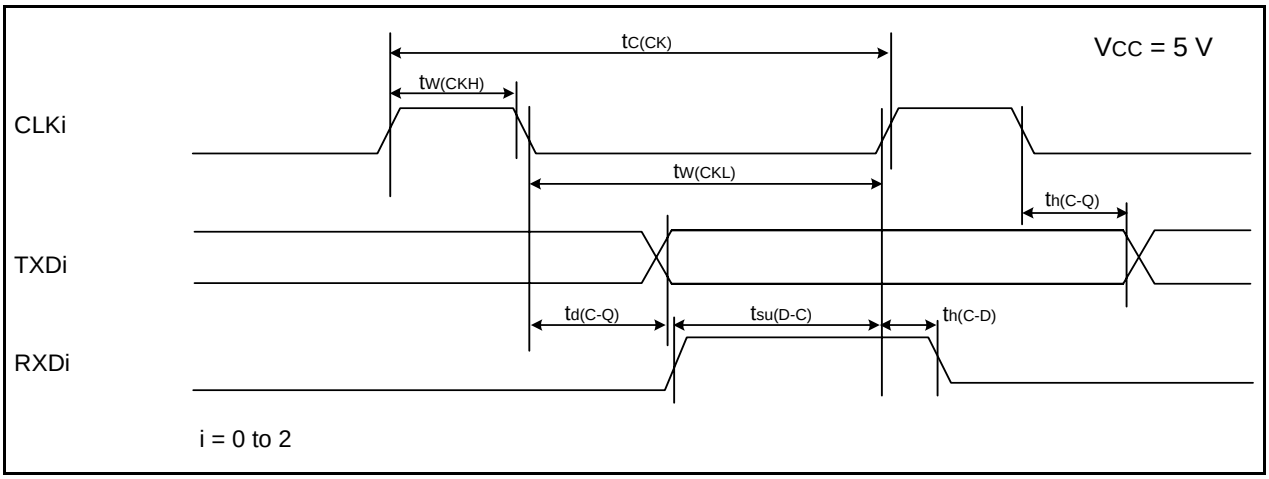


Figure 5.11 Serial Interface Timing Diagram when V_{CC} = 5 V

Table 5.23 External Interrupt $\overline{INTi}$ (i = 0 to 4) Input, Key Input Interrupt $\overline{KIi}$ (i = 0 to 3)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{W(INH)}$	$\overline{INTi}$ input “H” width, $\overline{KIi}$ input “H” width	250 (1)	—	ns
$t_{W(INL)}$	$\overline{INTi}$ input “L” width, $\overline{KIi}$ input “L” width	250 (2)	—	ns

Notes:
1. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

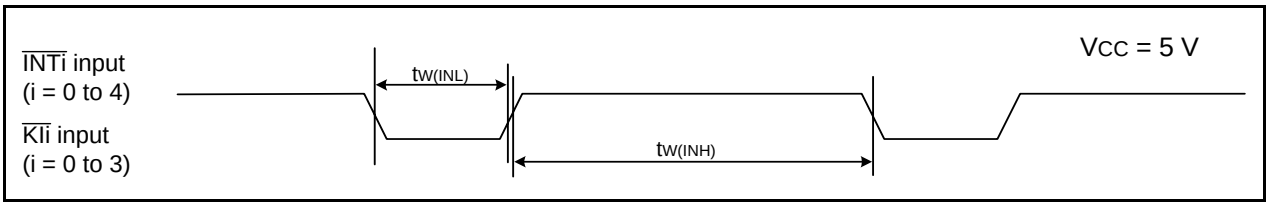


Figure 5.12 Input Timing Diagram for External Interrupt $\overline{INTi}$ and Key Input Interrupt $\overline{KIi}$ when V_{CC} = 5 V

Table 5.24 Electrical Characteristics (3) [2.7 V ≤ Vcc < 4.2 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Other than XOUT	Drive capacity High	I_{OH} = –5 mA	V_{CC} – 0.5	—	V_{CC}	V
			Drive capacity Low	I_{OH} = –1 mA	V_{CC} – 0.5	—	V_{CC}	V
		XOUT		I_{OH} = –200 μA	1.0	—	V_{CC}	V
V_{OL}	Output “L” voltage	Other than XOUT	Drive capacity High	I_{OL} = 5 mA	—	—	0.5	V
			Drive capacity Low	I_{OL} = 1 mA	—	—	0.5	V
		XOUT		I_{OL} = 200 μA	—	—	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT2}$, $\overline{INT3}$, $\overline{INT4}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, TRBO, TRCIOA, TRCIOB, TRCIOC, TRCIOD, TRDIOA0, TRDIOB0, TRDIOC0, TRDIOD0, TRDIOA1, TRDIOB1, TRDIOC1, TRDIOD1, TRCTRG, TRCCLK, TRFI, $\overline{TRGIOA}$, TRGIOB, $\overline{ADTRG}$, RXD0, RXD1, RXD2, CLK0, CLK1, CLK2, SSI, SCL, SDA, SSO	V_{CC} = 3.0 V		0.1	0.4	—	V
		$\overline{RESET}$	V_{CC} = 3.0 V		0.1	0.5	—	V
I_{IH}	Input “H” current		V_I = 3 V, V_{CC} = 3.0 V		—	—	4.0	μA
I_{IL}	Input “L” current		V_I = 0 V, V_{CC} = 3.0 V		—	—	–4.0	μA
R_{PULLUP}	Pull-up resistance		V_I = 0 V, V_{CC} = 3.0 V		42	84	168	kΩ
R_{fXIN}	Feedback resistance	XIN			—	0.3	—	MΩ
R_{fXCIN}	Feedback resistance	XCIN			—	8	—	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	—	—	V

Note:
1. 2.7 V ≤ V_{CC} < 4.2 V, T_{opr} = –20 to 85 °C (N version)/–40 to 85 °C (D version), and f(XIN) = 10 MHz, unless otherwise specified.

Table 5.31 Electrical Characteristics (5) [1.8 V ≤ Vcc < 2.7 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Other than XOUT	Drive capacity High	I_{OH} = –2 mA	V_{CC} – 0.5	—	V_{CC}	V
			Drive capacity Low	I_{OH} = –1 mA	V_{CC} – 0.5	—	V_{CC}	V
		XOUT		I_{OH} = –200 μA	1.0	—	V_{CC}	V
V_{OL}	Output “L” voltage	Other than XOUT	Drive capacity High	I_{OL} = 2 mA	—	—	0.5	V
			Drive capacity Low	I_{OL} = 1 mA	—	—	0.5	V
		XOUT		I_{OL} = 200 μA	—	—	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT2}$, $\overline{INT3}$, $\overline{INT4}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, TRBO, TRCIOA, TRCIOB, TRCIOC, TRCIOD, TRDIOA0, TRDIOB0, TRDIOC0, TRDIOD0, TRDIOA1, TRDIOB1, TRDIOC1, TRDIOD1, TRCTRG, TRCCLK, TRFI, $\overline{TRGIOA}$, TRGIOB, $\overline{ADTRG}$, RXD0, RXD1, RXD2, CLK0, CLK1, CLK2, SSI, SCL, SDA, SSO			0.05	0.20	—	V
		$\overline{RESET}$			0.05	0.20	—	V
I_{IH}	Input “H” current		V_I = 2.2 V, V_{CC} = 2.2 V		—	—	4.0	μA
I_{IL}	Input “L” current		V_I = 0 V, V_{CC} = 2.2 V		—	—	–4.0	μA
R_{PULLUP}	Pull-up resistance		V_I = 0 V, V_{CC} = 2.2 V		70	140	300	kΩ
R_{fXIN}	Feedback resistance	XIN			—	0.3	—	MΩ
R_{fXCIN}	Feedback resistance	XCIN			—	8	—	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	—	—	V

Note:
1. 1.8 V ≤ V_{CC} < 2.7 V, T_{opr} = –20 to 85 °C (N version)/–40 to 85 °C (D version), and f(XIN) = 5 MHz, unless otherwise specified.

Table 5.36 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	800	—	ns
$t_{W(CKH)}$	CLKi input “H” width	400	—	ns
$t_{W(CKL)}$	CLKi input “L” width	400	—	ns
$t_{d(C-Q)}$	TXDi output delay time	—	200	ns
$t_{h(C-Q)}$	TXDi hold time	0	—	ns
$t_{su(D-C)}$	RXDi input setup time	150	—	ns
$t_{h(C-D)}$	RXDi input hold time	90	—	ns

i = 0 to 2

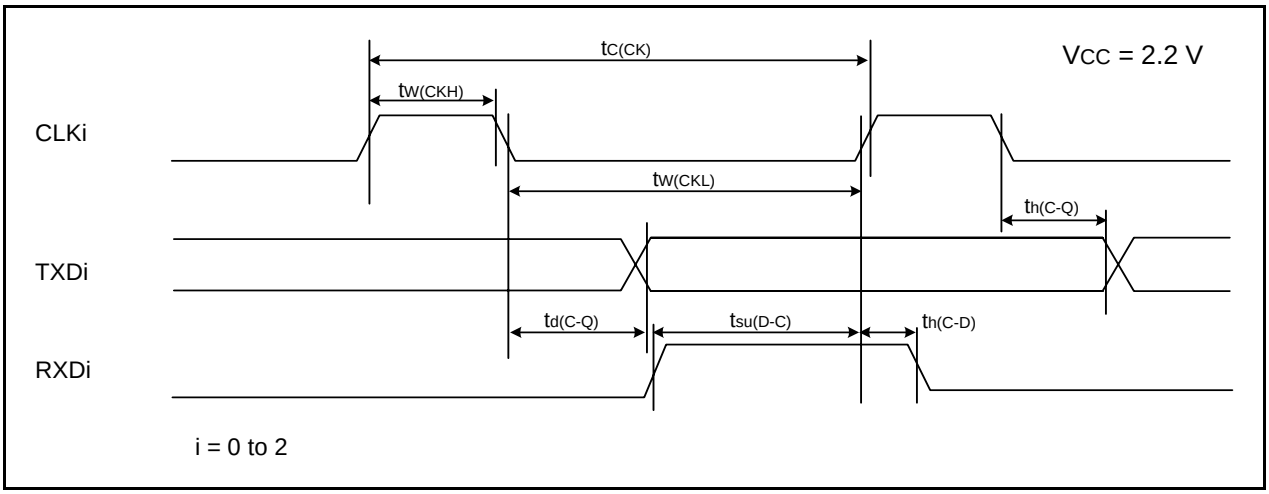


Figure 5.21 Serial Interface Timing Diagram when Vcc = 2.2 V

Table 5.37 External Interrupt $\overline{INTi}$ (i = 0 to 4) Input, Key Input Interrupt $\overline{KIi}$ (i = 0 to 3)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{W(INH)}$	$\overline{INTi}$ input “H” width, $\overline{KIi}$ input “H” width	1000 (1)	—	ns
$t_{W(INL)}$	$\overline{INTi}$ input “L” width, $\overline{KIi}$ input “L” width	1000 (2)	—	ns

Notes:
1. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

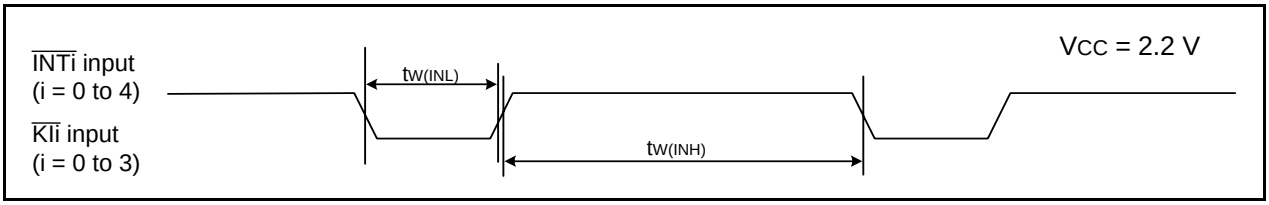


Figure 5.22 Input Timing Diagram for External Interrupt $\overline{INTi}$ and Key Input Interrupt $\overline{KIi}$ when Vcc = 2.2 V

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